

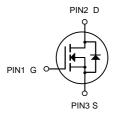
Description

The Si2308BDS-T1-E3 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

 V_{DS} = 60V I_D = 3A $R_{DS(ON)}$ < 85m Ω @ V_{GS} =10V



Application

Battery protection

Load switch

Uninterruptible power supply

N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
Si2308BDS-T1-E3	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	60	V
V _G s	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	3	А
Ім	Drain Current-Pulsed (Note 1)	10	А
P _D	Maximum Power Dissipation	1.7	W
TJ,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	73.5	°C/W



N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=250\mu A$ 0.		1.3	2.0	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =3A	-	72	85	mΩ	
Dialii-Source Oil-State Resistance		V _{GS} =4.5V, I _D =1.5A	-	85	103	mΩ	
Forward Transconductance	g FS	V _{DS} =15V,I _D =2A		3	-	S	
Dynamic Characteristics (Note4)							
Input Capacitance	C _{lss}	V _{DS} =30V,V _{GS} =0V,	-	510	-	PF	
Output Capacitance	Coss	F=1.0MHz	-	34	-	PF	
Reverse Transfer Capacitance	C _{rss}	F = 1.000112	-	26	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	6	-	nS	
Turn-on Rise Time	t _r	V _{DD} =30V,I _D =1.5A	-	15	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{GEN} =1 Ω	-	15	-	nS	
Turn-Off Fall Time	t _f		-	10	-	nS	
Total Gate Charge	Q_g	V _{DS} =30V,I _D =3A,	-	7.5	-	nC	
Gate-Source Charge	Q _{gs}	V_{DS} =30V, I_D =3A, V_{GS} =4.5V	-	1.4	-	nC	
Gate-Drain Charge	Q_{gd}	V _{GS} -4.5V	-	3	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =3A	-	-	1.2	V	
Diode Forward Current (Note 2)	Is		-	-	3	Α	

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

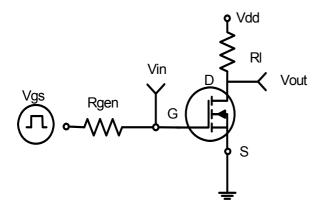
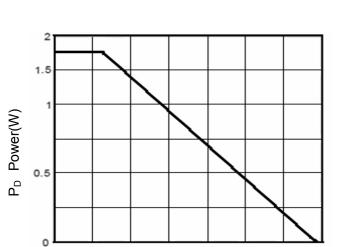


Figure 1:Switching Test Circuit



 T_J -Junction Temperature($^{\circ}$ C)

0

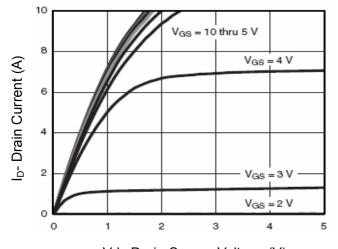
20

Figure 3 Power Dissipation

100

120

140



Vds Drain-Source Voltage (V)

Figure 5 Output Characteristics

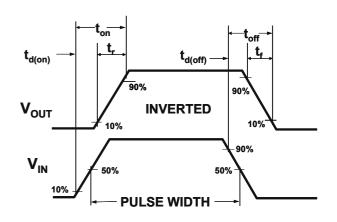


Figure 2:Switching Waveforms

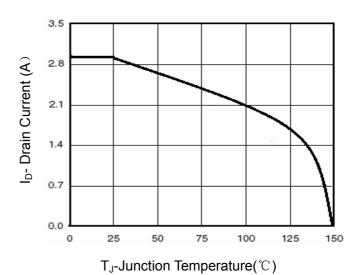


Figure 4 Drain Current

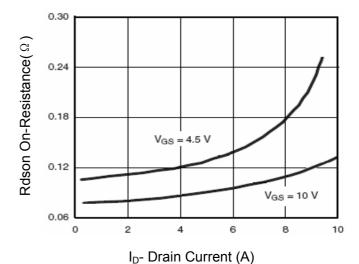


Figure 6 Drain-Source On-Resistance



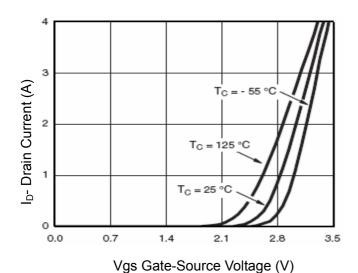
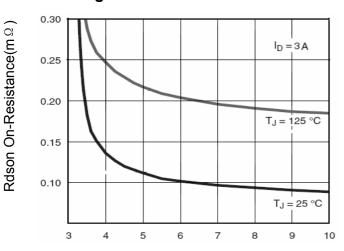
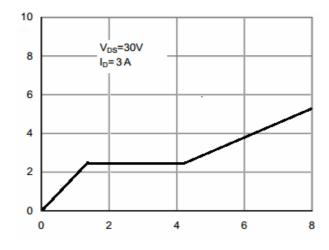


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs



Vgs Gate-Source Voltage (V)

Qg Gate Charge (nC) Figure 11 Gate Charge

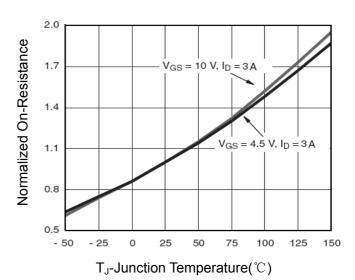
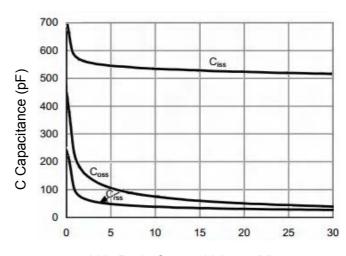
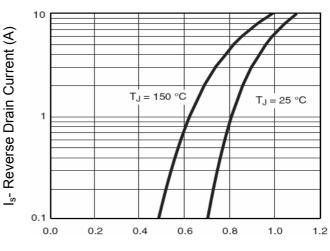


Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward

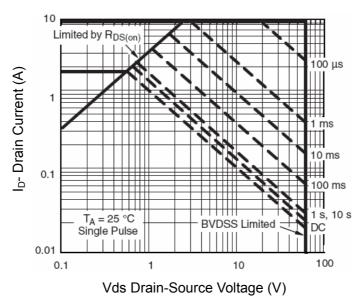


Figure 13 Safe Operation Area

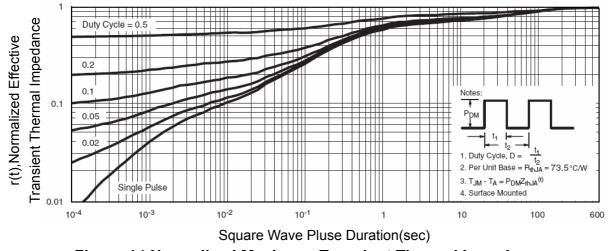
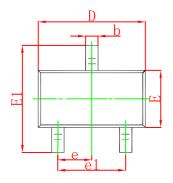
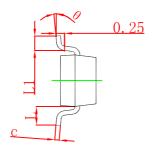
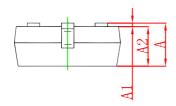


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Outline Dimensions

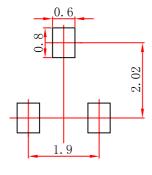






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



- Note:
 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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